

TABLE OF CONTENTS

Features	1	Absolute Maximum Ratings	5
Applications	1	Thermal Resistance	5
General Description	1	ESD Caution	5
Pin Configurations	1	Typical Performance Characteristics	6
Revision History	2	Outline Dimensions	12
Specifications	3	Ordering Guide	14

REVISION HISTORY

7/11—Rev. A to Rev. B

Change to Features and General Description Sections	1
Updated Outline Dimensions	12
Changes to Ordering Guide	13
Added Automotive Products Section	13

10/06—Rev. 0 to Rev. A

Added AD8665	Universal
Added New Figure 1 and Figure 2, Renumbered Sequentially	1
Changes to Table 4	5
Changes to Figure 8, Figure 9, and Figure 11	6
Change to Figure 40	11
Updated Outline Dimensions	12
Changes to Ordering Guide	13

4/06—Rev 0: Initial Version

SPECIFICATIONS

$V_{DD} = 5.0\text{ V}$, $V_{CM} = V_{DD}/2$, $T_A = 25^\circ\text{C}$, unless otherwise noted.

Table 1.

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	V_{OS}	$V_{CM} = 2.5\text{ V}$ $V_{CM} = -0.1\text{ V to }+3.0\text{ V}$ $-40^\circ\text{C} < T_A < +125^\circ\text{C}$		0.7	2.5	mV
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		3.0	10	$\mu\text{V}/^\circ\text{C}$
Input Bias Current	I_B	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		0.2	1	pA
Input Offset Current	I_{OS}	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		0.1	0.5	pA
Input Voltage Range	V_{CM}	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$	-0.1		+3.0	V
Common-Mode Rejection Ratio	CMRR	$V_{CM} = -0.1\text{ V to }+3.0\text{ V}$ $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	84	100		dB
Large-Signal Voltage Gain	A_{VO}	$R_L = 2\text{ k}\Omega$, $V_O = 0.5\text{ V to }4.5\text{ V}$	79	145		dB
OUTPUT CHARACTERISTICS						
Output Voltage High	V_{OH}	$I_{OUT} = 1\text{ mA}$ $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	4.88	4.93		V
Output Voltage Low	V_{OL}	$I_{OUT} = 1\text{ mA}$ $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	4.86	50	85	V
Short-Circuit Output Current	I_{SC}			± 19	105	mV
Closed-Loop Output Impedance	Z_{OUT}	At 1 MHz, $A_V = 1$		50		mA
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_{DD} = 5.0\text{ V to }16\text{ V}$ $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	98	115		dB
Supply Current per Amplifier	I_{SY}	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$	94	1.1	1.4	dB
					2.0	mA
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_L = 2\text{ k}\Omega$		3.5		$\text{V}/\mu\text{s}$
Gain Bandwidth Product	GBP			4		MHz
Phase Margin	Φ_M			70		Degrees
NOISE PERFORMANCE						
Peak-to-Peak Noise	$e_n\text{ p-p}$	0.1 Hz to 10 Hz		2.4		$\mu\text{V p-p}$
Voltage Noise Density	e_n	$f = 1\text{ kHz}$ $f = 10\text{ kHz}$		10		$\text{nV}/\sqrt{\text{Hz}}$
Channel Separation	CS	$f = 10\text{ kHz}$		8		$\text{nV}/\sqrt{\text{Hz}}$
				-115		dB

AD8665/AD8666/AD8668

$V_{DD} = 16\text{ V}$, $V_{CM} = V_{DD}/2$, $T_A = 25^\circ\text{C}$, unless otherwise noted.

Table 2.

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	V_{OS}	$V_{CM} = 8\text{ V}$ $V_{CM} = -0.1\text{ V to }+14.0\text{ V}$ $-40^\circ\text{C} < T_A < +125^\circ\text{C}$		0.6	2.5 3.0 5.0	mV mV mV
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		3.0	10	$\mu\text{V}/^\circ\text{C}$
Input Bias Current	I_B	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		0.2	1	pA
Input Offset Current	I_{OS}	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$			550	pA
		$-40^\circ\text{C} < T_A < +125^\circ\text{C}$		0.1	0.5	pA
Input Voltage Range	V_{CM}	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$	-0.1		70	pA
Common-Mode Rejection Ratio	CMRR	$V_{CM} = -0.1\text{ V to }+14.0\text{ V}$ $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	90	110	+14.0	V dB
Large-Signal Voltage Gain	A_{VO}	$R_L = 2\text{ k}\Omega$, $V_O = 0.5\text{ V to }15.5\text{ V}$	80			dB
			130	255		V/mV
OUTPUT CHARACTERISTICS						
Output Voltage High	V_{OH}	$I_{OUT} = 1\text{ mA}$ $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	15.94	15.96		V
Output Voltage Low	V_{OL}	$I_{OUT} = 1\text{ mA}$ $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	15.90	22	40	V mV
Short-Circuit Output Current	I_{SC}				50	mV
Closed-Loop Output Impedance	Z_{OUT}	At 1 MHz, $A_V = 1$		± 140		mA
				50		Ω
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$V_{DD} = 5.0\text{ V to }16\text{ V}$ $-40^\circ\text{C} < T_A < +125^\circ\text{C}$	98	115		dB
Supply Current per Amplifier	I_{SY}	$-40^\circ\text{C} < T_A < +125^\circ\text{C}$	94			dB
				1.15	1.55	mA
					2.0	mA
DYNAMIC PERFORMANCE						
Slew Rate	SR	$R_L = 2\text{ k}\Omega$		3.5		V/ μs
Gain Bandwidth Product	GBP			4		MHz
Phase Margin	Φ_M			73		Degrees
NOISE PERFORMANCE						
Peak-to-Peak Noise	$e_n\text{ p-p}$	0.1 Hz to 10 Hz		2.5		$\mu\text{V p-p}$
Voltage Noise Density	e_n	$f = 1\text{ kHz}$ $f = 10\text{ kHz}$		10		nV/ $\sqrt{\text{Hz}}$ nV/ $\sqrt{\text{Hz}}$
Channel Separation	CS	$f = 10\text{ kHz}$		-115		dB

ABSOLUTE MAXIMUM RATINGS

Table 3.

Parameter	Rating
Supply Voltage	18 V
Input Voltage	GND to V_{DD}
Differential Input Voltage	± 18 V
Output Short-Circuit to GND	Indefinite
Storage Temperature Range	-65°C to $+150^{\circ}\text{C}$
Operating Temperature Range	-40°C to $+125^{\circ}\text{C}$
Lead Temperature (Soldering, 60 sec)	300°C
Junction Temperature	150°C

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

THERMAL RESISTANCE

Table 4. Thermal Resistance

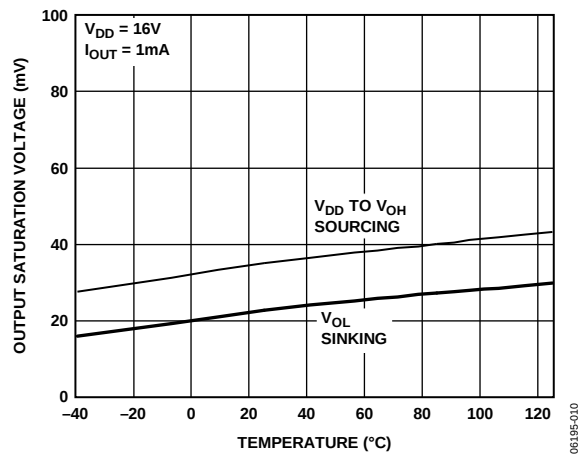
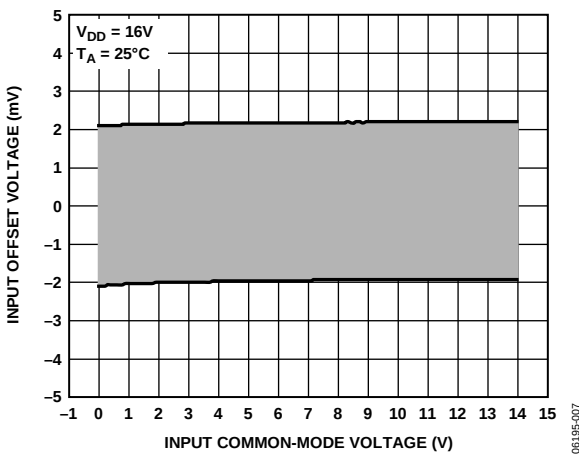
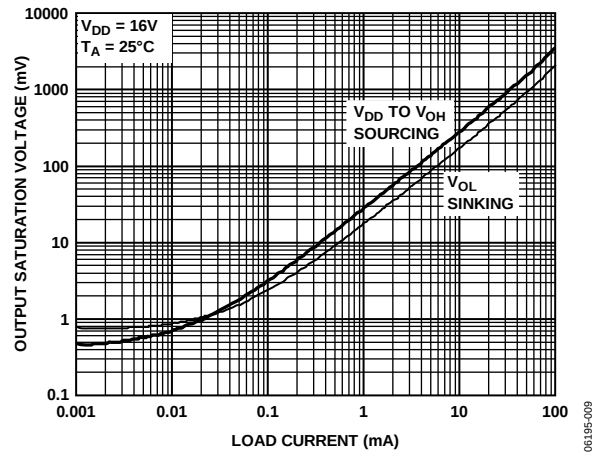
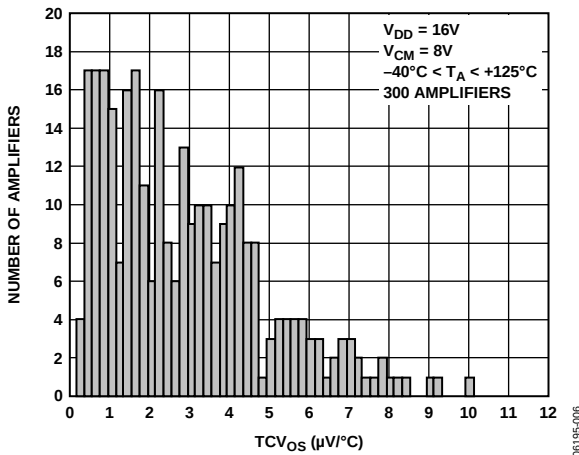
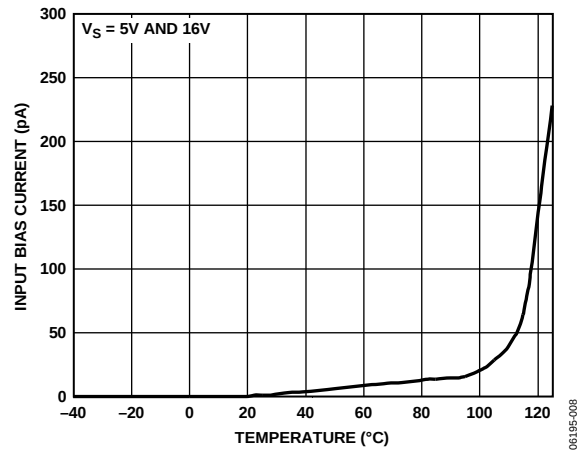
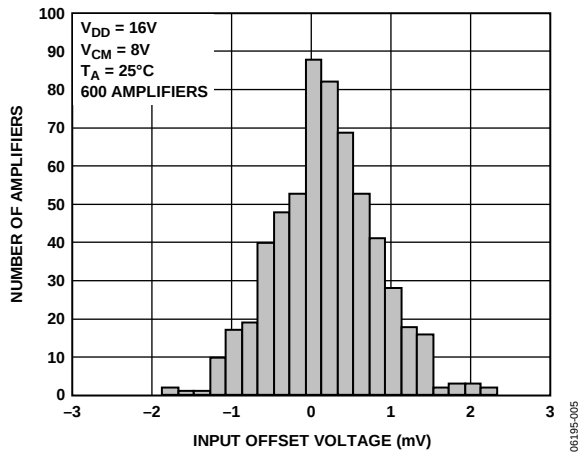
Package Type	θ_{JA}	θ_{JC}	Unit
5-Lead SOT-23 (RJ-5)	240	92	$^{\circ}\text{C}/\text{W}$
8-Lead SOIC_N (R-8)	158	43	$^{\circ}\text{C}/\text{W}$
8-Lead MSOP (RM-8)	210	45	$^{\circ}\text{C}/\text{W}$
14-Lead SOIC (R-14)	120	36	$^{\circ}\text{C}/\text{W}$
14-Lead TSSOP (RU-14)	180	35	$^{\circ}\text{C}/\text{W}$

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

TYPICAL PERFORMANCE CHARACTERISTICS



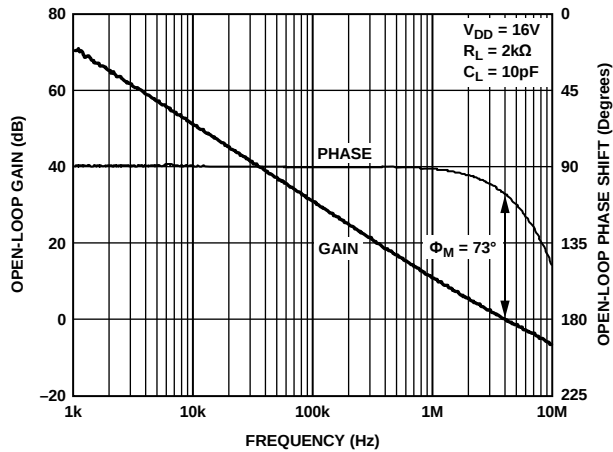


Figure 13. Open-Loop Gain and Phase vs. Frequency

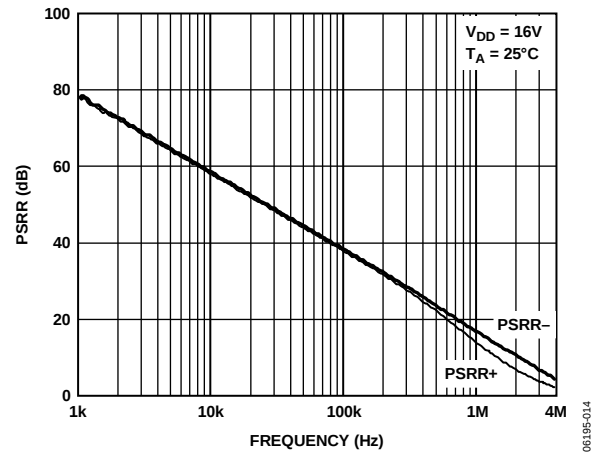


Figure 16. Power Supply Rejection Ratio vs. Frequency

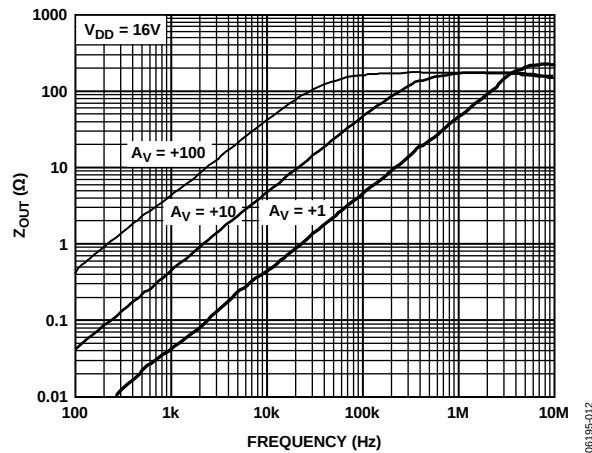


Figure 14. Closed-Loop Output Impedance vs. Frequency

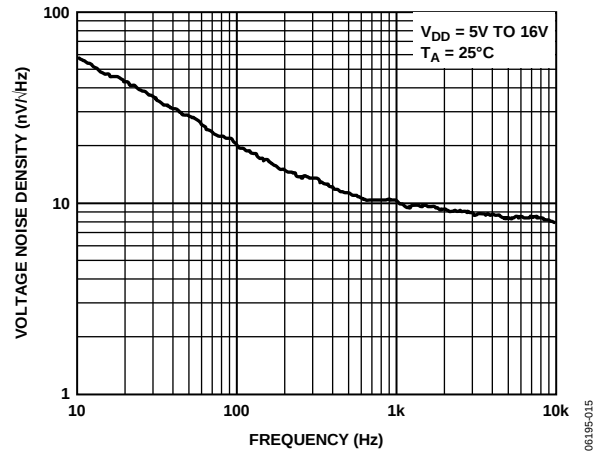


Figure 17. Voltage Noise Density vs. Frequency

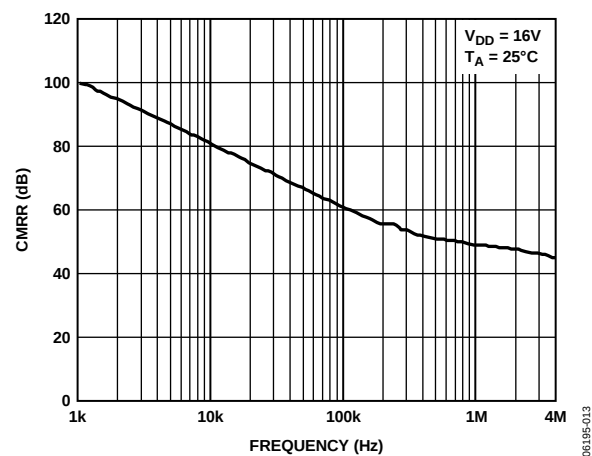


Figure 15. Common-Mode Rejection Ratio vs. Frequency

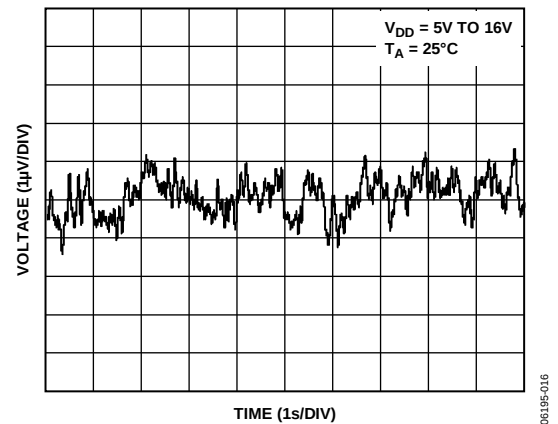


Figure 18. 0.1 Hz to 10 Hz Voltage Noise

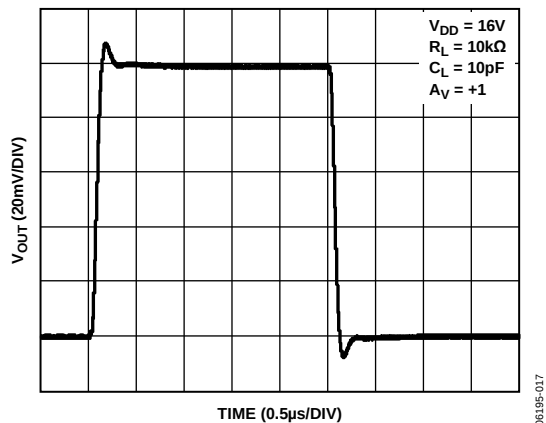


Figure 19. Small-Signal Transient Response

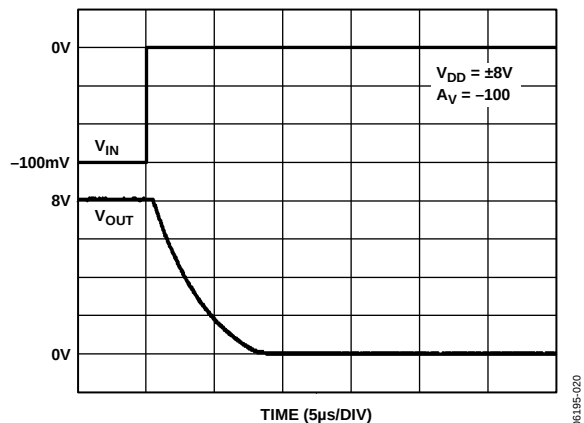


Figure 22. Positive Overload Recovery Time

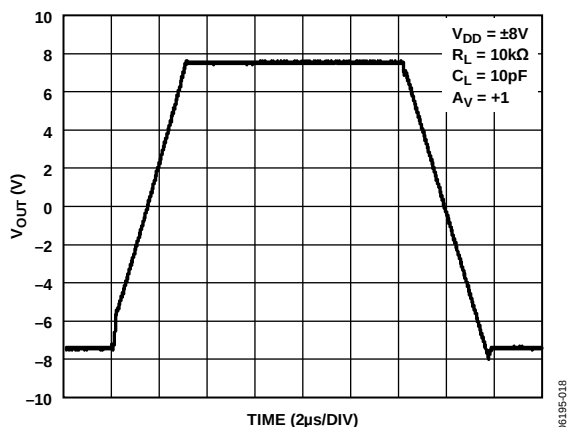


Figure 20. Large-Signal Transient Response

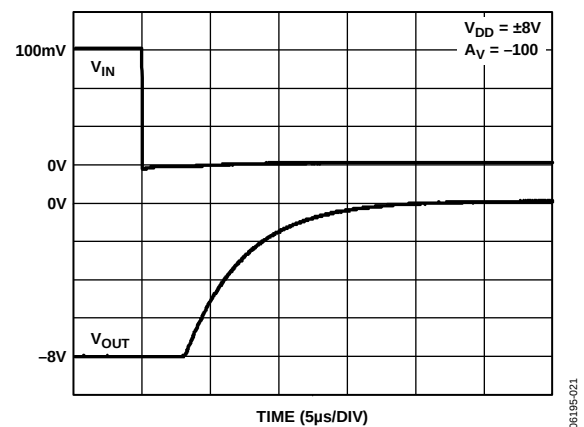


Figure 23. Negative Overload Recovery Time

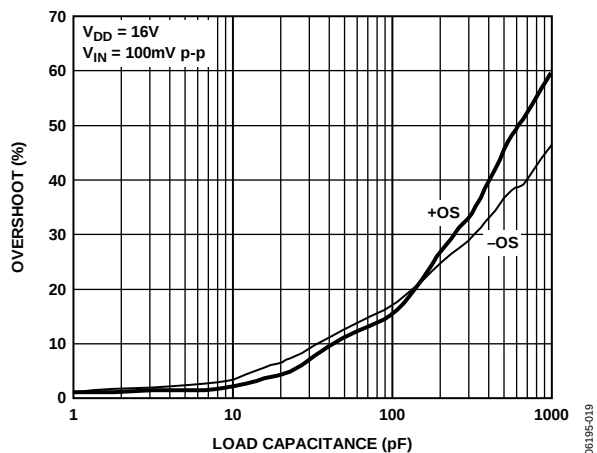


Figure 21. Small-Signal Overshoot vs. Load Capacitance

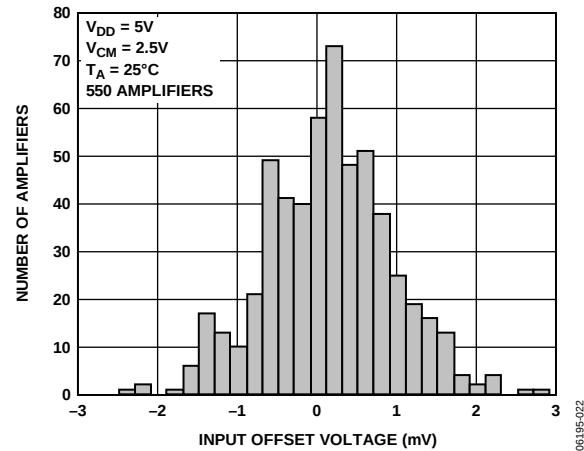


Figure 24. Input Offset Voltage Distribution

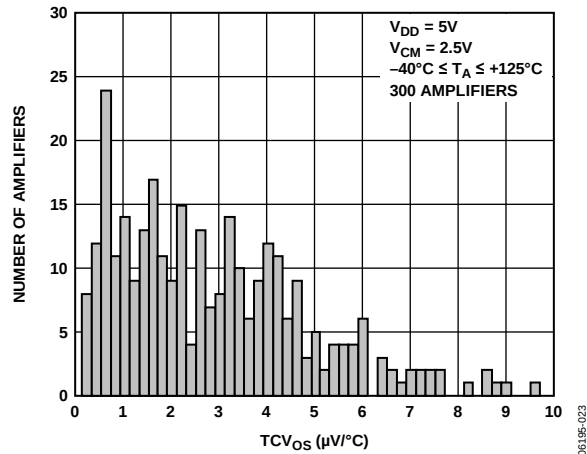


Figure 25. V_{OS} Drift (TCV_{OS}) Distribution

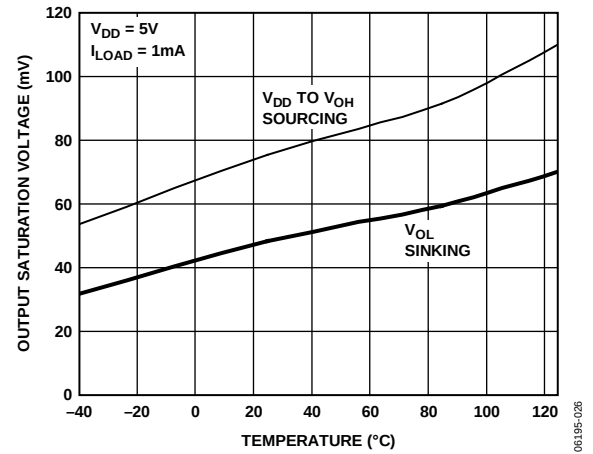


Figure 28. Output Saturation Voltage vs. Temperature

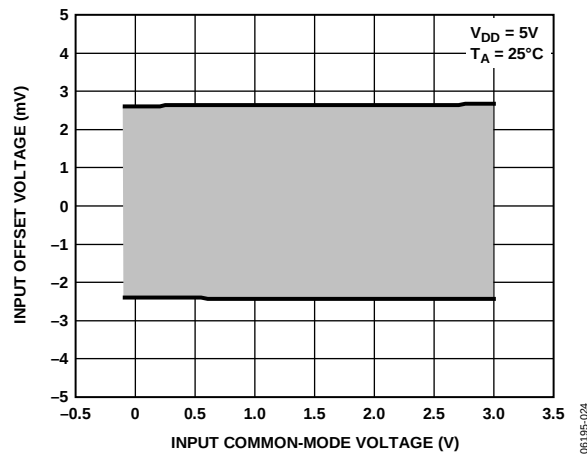


Figure 26. Offset Voltage vs. Common-Mode Voltage

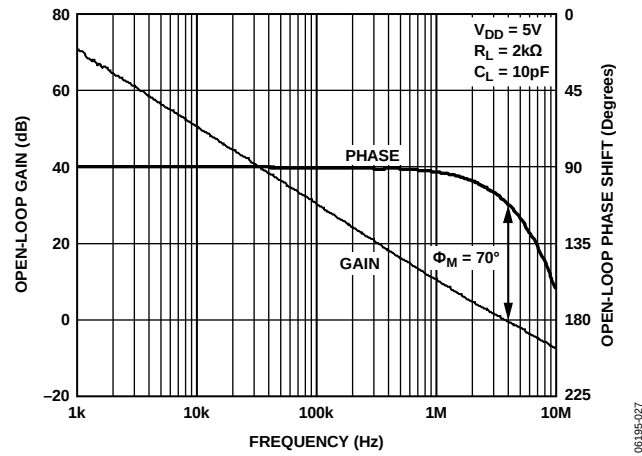


Figure 29. Open-Loop Gain and Phase vs. Frequency

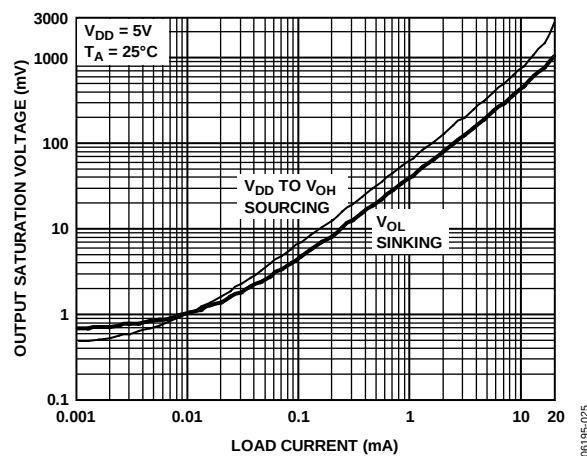


Figure 27. Output Saturation Voltage vs. Load Current

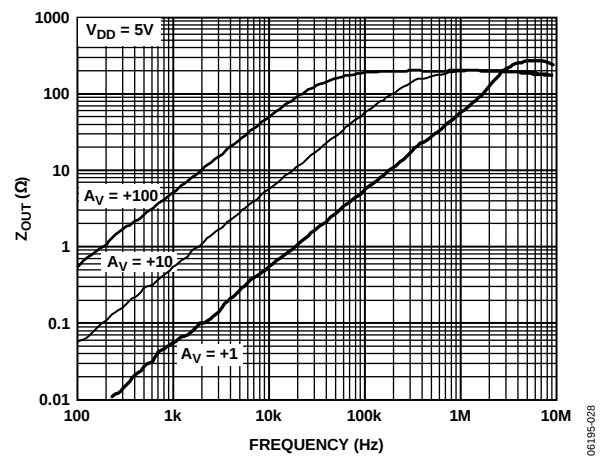


Figure 30. Closed-Loop Output Impedance vs. Frequency

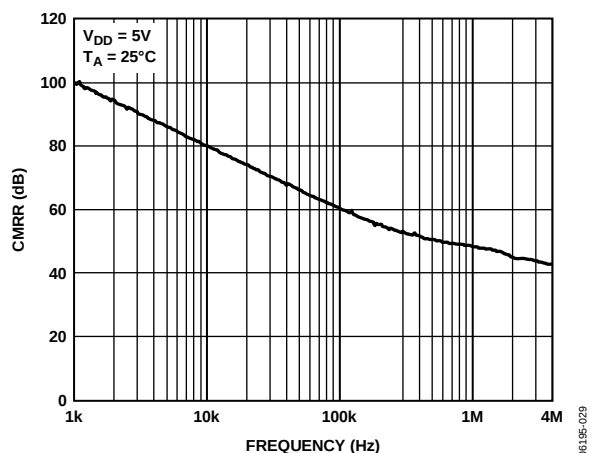


Figure 31. Common-Mode Rejection Ratio vs. Frequency

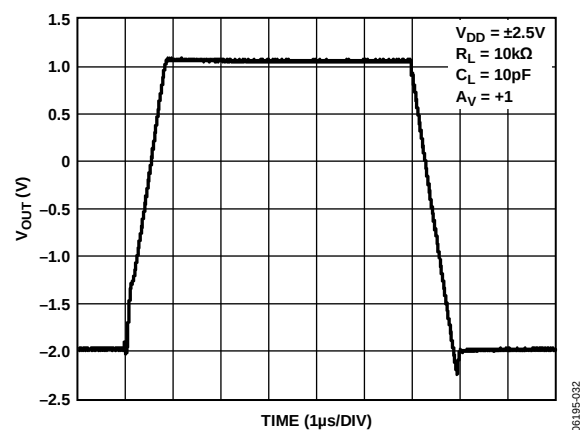


Figure 34. Large-Signal Transient Response

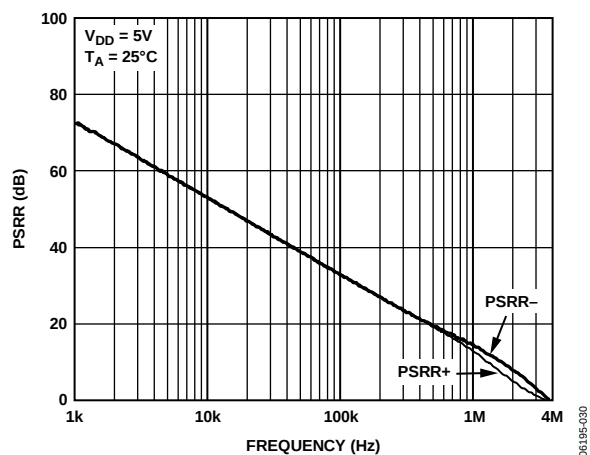


Figure 32. Power Supply Rejection Ratio vs. Frequency

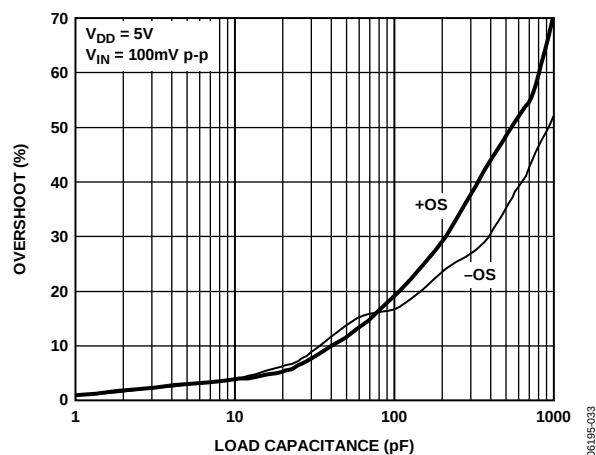


Figure 35. Small-Signal Overshoot vs. Load Capacitance

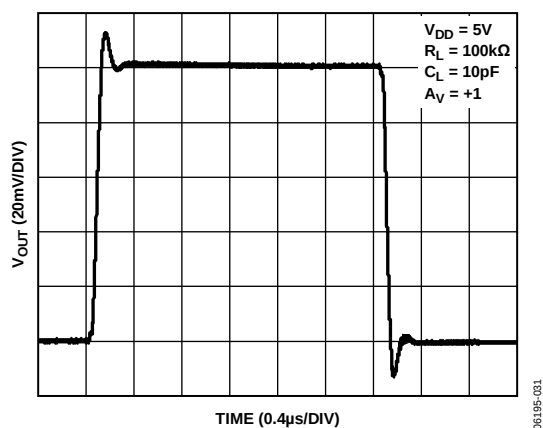


Figure 33. Small-Signal Transient Response

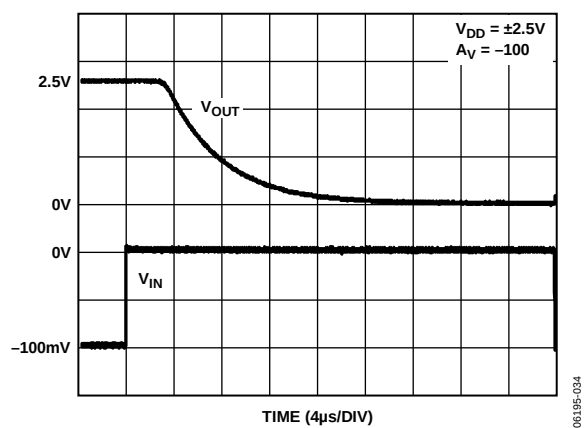


Figure 36. Positive Overload Recovery Time

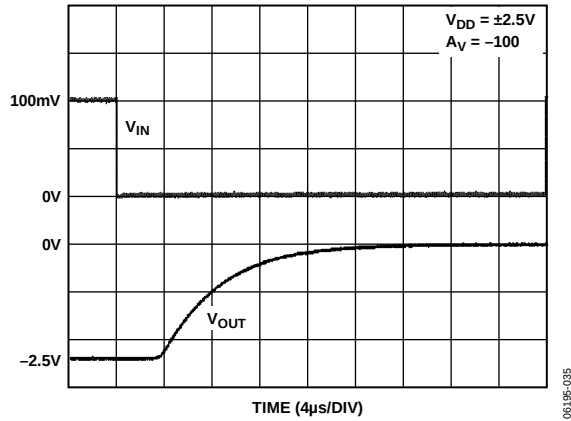


Figure 37. Negative Overload Recovery Time

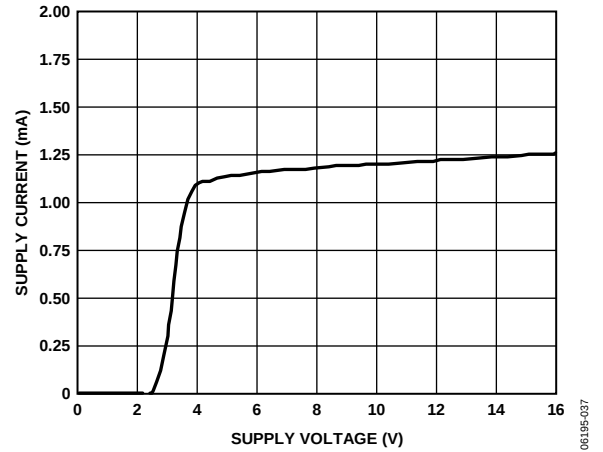


Figure 39. Supply Current vs. Supply Voltage

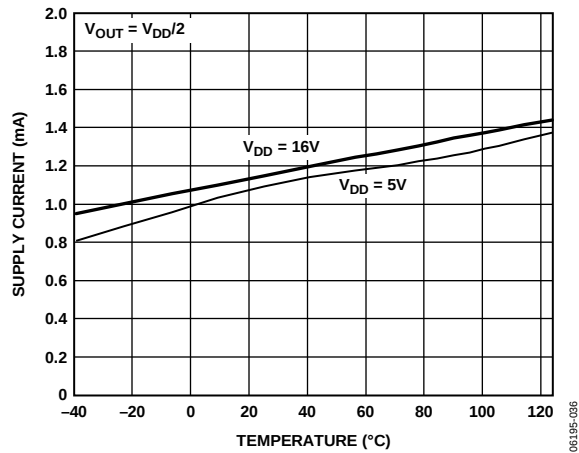


Figure 38. Supply Current vs. Temperature

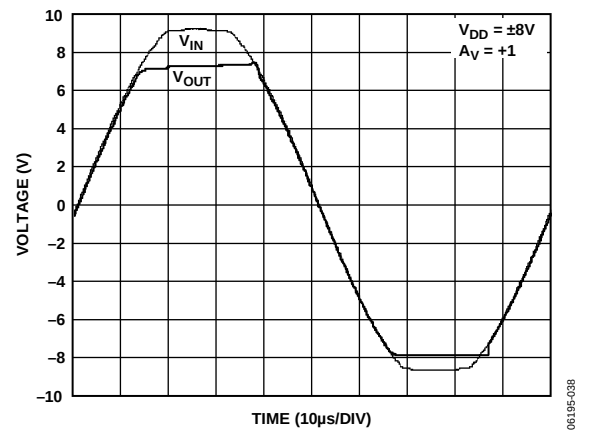
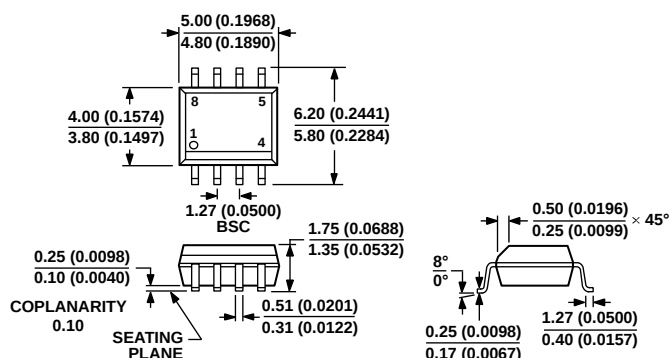


Figure 40. No Output Phase Reversal

OUTLINE DIMENSIONS

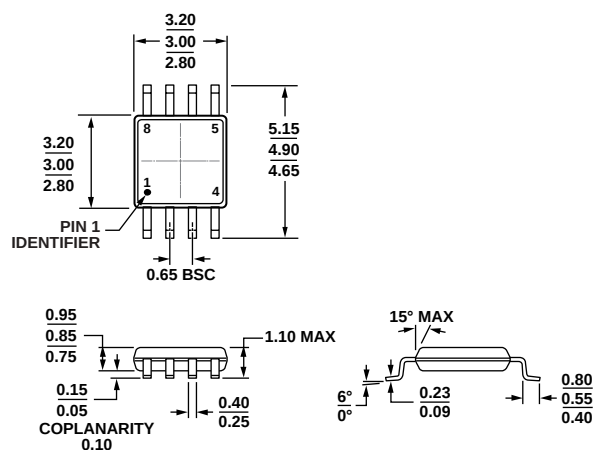


COMPLIANT TO JEDEC STANDARDS MS-012-AA

CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 41. 8-Lead Standard Small Outline Package [SOIC_N]
Narrow Body
(R-8)

Dimensions shown in millimeters and (inches)



COMPLIANT TO JEDEC STANDARDS MO-187-AA

Figure 42. 8-Lead Mini Small Outline Package [MSOP]
(RM-8)

Dimensions shown in millimeters

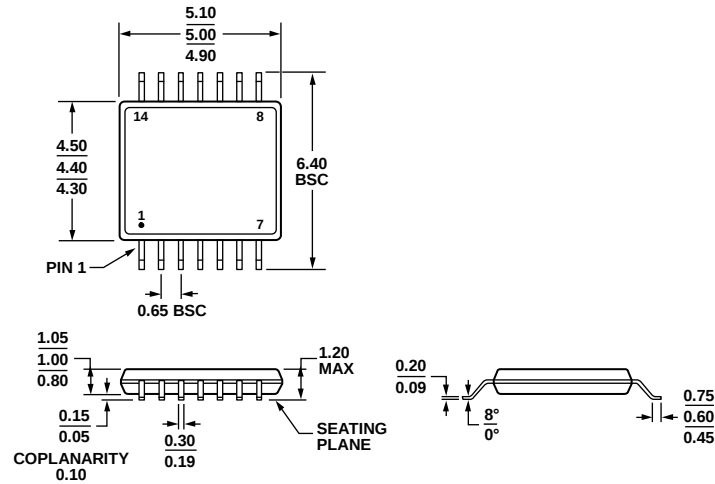
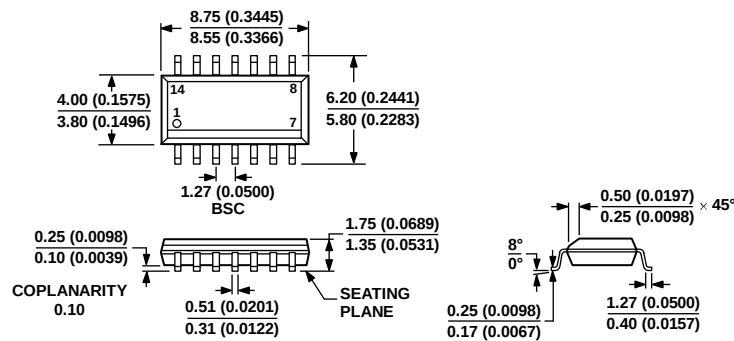


Figure 43. 14-Lead Thin Shrink Small Outline Package [TSSOP]
(RU-14)

Dimensions shown in millimeters

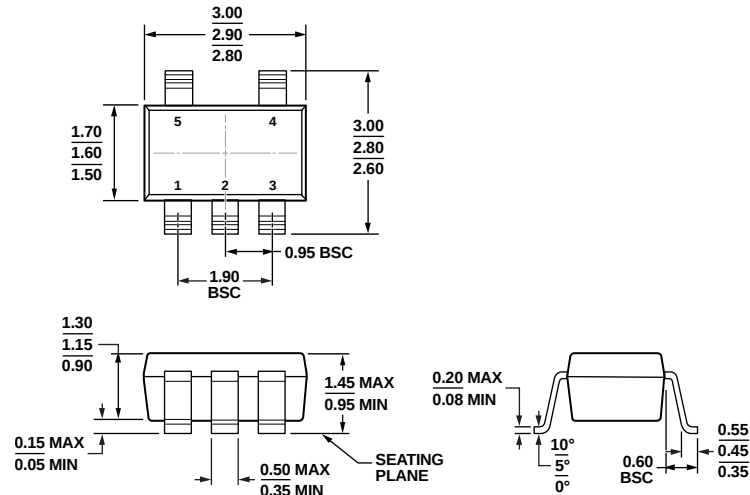


CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS
(IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR
REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN.

Figure 44. 14-Lead Standard Small Outline Package [SOIC_N]
Narrow Body
(R-14)

Dimensions shown in millimeters and (inches)

AD8665/AD8666/AD8668



COMPLIANT TO JEDEC STANDARDS MO-178-AA

Figure 45. 5-Lead Small Outline Transistor Package [SOT-23]
(RJ-5)

Dimensions shown in millimeters

11-01-2010-A

ORDERING GUIDE

Model ^{1, 2}	Temperature Range	Package Description	Package Option	Branding
AD8665ARZ	−40°C to +125°C	8-Lead SOIC_N	R-8	A1B
AD8665ARZ-REEL	−40°C to +125°C	8-Lead SOIC_N	R-8	
AD8665ARZ-REEL7	−40°C to +125°C	8-Lead SOIC_N	R-8	
AD8665ARJZ-R2	−40°C to +125°C	5-Lead SOT-23	RJ-5	
AD8665ARJZ-REEL	−40°C to +125°C	5-Lead SOT-23	RJ-5	
AD8665ARJZ-REEL7	−40°C to +125°C	5-Lead SOT-23	RJ-5	
AD8666ARZ	−40°C to +125°C	8-Lead SOIC_N	R-8	A16
AD8666ARZ-REEL	−40°C to +125°C	8-Lead SOIC_N	R-8	
AD8666ARZ-REEL7	−40°C to +125°C	8-Lead SOIC_N	R-8	
AD8666ARMZ	−40°C to +125°C	8-Lead MSOP	RM-8	
AD8666ARMZ-REEL	−40°C to +125°C	8-Lead MSOP	RM-8	
AD8666WARZ-R7	−40°C to +125°C	8-Lead SOIC_N	R-8	
AD8666WARZ-RL	−40°C to +125°C	8-Lead SOIC_N	R-8	
AD8668ARZ	−40°C to +125°C	14-Lead SOIC_N	R-14	
AD8668ARZ-REEL	−40°C to +125°C	14-Lead SOIC_N	R-14	
AD8668ARZ-REEL7	−40°C to +125°C	14-Lead SOIC_N	R-14	
AD8668ARUZ	−40°C to +125°C	14-Lead TSSOP	RU-14	
AD8668ARUZ-REEL	−40°C to +125°C	14-Lead TSSOP	RU-14	
AD8668WARUZ-R7	−40°C to +125°C	14-Lead TSSOP	RU-14	
AD8668WARUZ-RL	−40°C to +125°C	14-Lead TSSOP	RU-14	

¹ Z = RoHS Compliant Model

² W = Qualified for Automotive Applications.

AUTOMOTIVE PRODUCTS

The AD8666W/AD8668W models are available with controlled manufacturing to support the quality and reliability requirements of automotive applications. Note that these automotive models may have specifications that differ from the commercial models; therefore, designers should review the Specifications section of this data sheet carefully. Only the automotive grade products shown are available for use in automotive applications. Contact your local Analog Devices account representative for specific product ordering information and to obtain the specific Automotive Reliability reports for these models.

NOTES

AD8665/AD8666/AD8668

NOTES